

# CBCS SCHEME

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BEC602

## Sixth Semester B.E./B.Tech. Degree Examination, Dec.2025/Jan.2026 VLSI Design and Testing

Time: 3 hrs.

Max. Marks: 100

*Note: 1. Answer any FIVE full questions, choosing ONE full question from each module.  
2. M : Marks , L: Bloom's level , C: Course outcomes.*

Module – 1			M	L	C
<b>Q.1</b>	<b>a.</b>	Implement CMOS logic for the following compound gates. i) $F = \overline{A(B+C)+DE}$ ii) $F = \overline{(A+B+C)D}$	<b>10</b>	<b>L3</b>	<b>CO1</b>
	<b>b.</b>	Implement and explain 2 i/p multiplexes using TG and also mention advantages of TG.	<b>10</b>	<b>L3</b>	<b>CO2</b>
<b>OR</b>					
<b>Q.2</b>	<b>a.</b>	Design flip-flop using multiplexes and inverter.	<b>08</b>	<b>L3</b>	<b>CO2</b>
	<b>b.</b>	Illustrate structural representation for 2 i/p NAND gates by adding performance parameter.	<b>04</b>	<b>L3</b>	<b>CO2</b>
	<b>c.</b>	Develop physical symbolic layout for the following. i) Inverter ii) Transmission Gate	<b>08</b>	<b>L3</b>	<b>CO2</b>
<b>Module – 2</b>					
<b>Q.3</b>	<b>a.</b>	Explain the working principle of nMOS enhancement nmos transistor.	<b>10</b>	<b>L2</b>	<b>CO1</b>
	<b>b.</b>	Define Body Effect. Illustrate how body effect alters the $V_t$ and give mathematical expressions.	<b>05</b>	<b>L3</b>	<b>CO1</b>
	<b>c.</b>	Discuss $\beta_n / \beta_p$ ratio effect on transfer characteristics.	<b>05</b>	<b>L3</b>	<b>CO1</b>
<b>OR</b>					
<b>Q.4</b>	<b>a.</b>	Draw schematic diagram of CMOS inverter and explain its D C Transfer characteristics.	<b>12</b>	<b>L3</b>	<b>CO1</b>
	<b>b.</b>	Illustrate the mechanism of Latch-up in CMOS and preventive measures.	<b>08</b>	<b>L3</b>	<b>CO1</b>
<b>Module – 3</b>					
<b>Q.5</b>	<b>a.</b>	Explain czochralski method for wafer processing.	<b>06</b>	<b>L2</b>	<b>CO1</b>
	<b>b.</b>	Discuss Lamda-based p-well design rules.	<b>06</b>	<b>L2</b>	<b>CO1</b>
	<b>c.</b>	Explain the Twin-tub process.	<b>08</b>	<b>L3</b>	<b>CO1</b>
<b>OR</b>					
<b>Q.6</b>	<b>a.</b>	Describe switching characteristics of CMOS inverter with equivalent circuits to determine fall and rise time.	<b>10</b>	<b>L3</b>	<b>CO3</b>
	<b>b.</b>	Explain in brief scaling principles of MOS transistor dimensions.	<b>10</b>	<b>L2</b>	<b>CO1</b>
<b>Module – 4</b>					
<b>Q.7</b>	<b>a.</b>	What are the advantages of Dynamic CMOS logic and explain the working of dynamic CMOS inverter with timing diagrams.	<b>08</b>	<b>L3</b>	<b>CO4</b>
	<b>b.</b>	Realize 2 inputs XOR / XNOR gate using cascode voltage switch logic.	<b>04</b>	<b>L3</b>	<b>CO4</b>
	<b>c.</b>	Implement 4 – way switch logic using Transmission gate and write layout version of CMOS logic.	<b>08</b>	<b>L3</b>	<b>CO4</b>

OR

<b>Q.8</b>	<b>a.</b>	Draw star connection for CMOS inverter layout optimization and mention its advantages.	<b>06</b>	<b>L3</b>	<b>CO4</b>
	<b>b.</b>	Find Euler's path for the function $Z = \overline{(A+B)+CD}$ and draw corresponding layout.	<b>06</b>	<b>L3</b>	<b>CO4</b>
	<b>c.</b>	Write short notes on : i) ESD Protection ii) Tristate and Bidirectional Pads.	<b>08</b>	<b>L2</b>	<b>CO4</b>

Module – 5

<b>Q.9</b>	<b>a.</b>	Implement AOI based clocked NOR SR Latch circuit with waveforms.	<b>10</b>	<b>L3</b>	<b>CO5</b>
	<b>b.</b>	Illustrate typical design flow of a contemporary and an ideal approach for designing system.	<b>10</b>	<b>L3</b>	<b>CO5</b>

OR

<b>Q.10</b>	<b>a.</b>	Illustrate J – K flip – flop with Nand gate JK latches with waveforms.	<b>10</b>	<b>L3</b>	<b>CO5</b>
	<b>b.</b>	Write short notes on : i) Adhoc Testing ii) Self Test and Build in Test.	<b>10</b>	<b>L2</b>	<b>CO1</b>

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